

# PJT138K

## 50V N-Channel Enhancement Mode MOSFET – ESD Protected

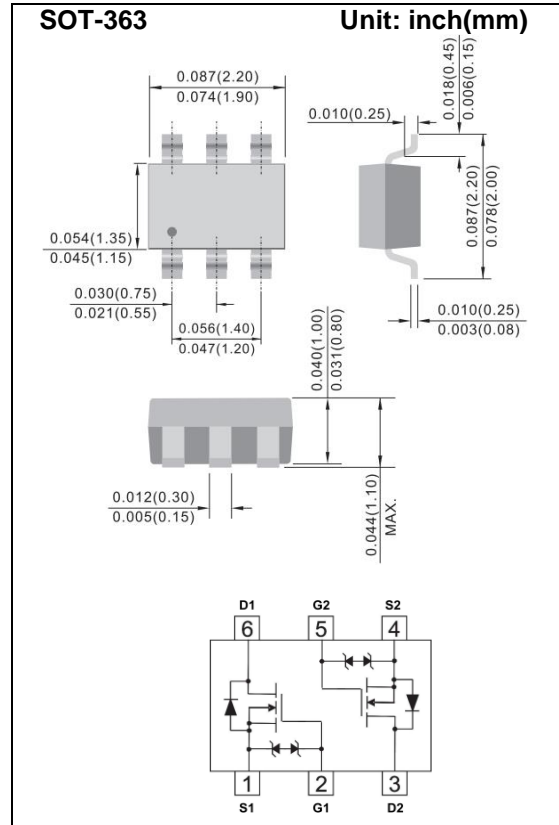
**Voltage** **50 V** **Current** **360mA**

### Features

- RDS(ON) , VGS@10V, ID@500mA<1.6Ω
- RDS(ON) , VGS@4.5V, ID@200mA<2.5Ω
- RDS(ON) , VGS@2.5V, ID@100mA<4.5Ω
- Advanced Trench Process Technology
- Specially Designed for Battery Operated Systems, Solid-State Relays Drivers: Relay, Displays, Memories, etc.
- ESD Protected 2KV HBM
- Lead free in compliance with EU RoHS 2011/65/EU directive
- Green molding compound as per IEC61249 Std. (Halogen Free)

### Mechanical Data

- Case : SOT-363 Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.00021 ounces, 0.006 grams



### Maximum Ratings and Thermal Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNITS	
Drain-Source Voltage	V <sub>DS</sub>	50	V	
Gate-Source Voltage	V <sub>GS</sub>	+20	V	
Continuous Drain Current	I <sub>D</sub>	360	mA	
Pulsed Drain Current	I <sub>DM</sub>	1200	mA	
Power Dissipation	P <sub>D</sub>	T <sub>A</sub> =25°C	236	mW
		Derate above 25°C	1.89	mW/°C
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55~150	°C	
Typical Thermal resistance	R <sub>θJA</sub>	530	°C/W	
- Junction to Ambient (Note 3)				

# PJT138K

## Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
<b>Static</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	50	-	-	V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	0.8	1.0	1.5	V
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =500mA	-	0.96	1.6	Ω
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =200mA	-	1.25	2.5	
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =100mA	-	2.73	4.5	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =50V, V <sub>GS</sub> =0V	-	0.01	1	uA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	±3.0	±10	uA
<b>Dynamic</b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =25V, I <sub>D</sub> =250mA, V <sub>GS</sub> =4.5V (Note 1,2)	-	0.63	1	nC
Gate-Source Charge	Q <sub>gs</sub>		-	0.2	-	
Gate-Drain Charge	Q <sub>gd</sub>		-	0.23	-	
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1.0MHZ	-	25	50	pF
Output Capacitance	C <sub>oss</sub>		-	9.5	20	
Reverse Transfer Capacitance	C <sub>rss</sub>		-	2.1	5	
<b>Switching</b>						
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =25V, I <sub>D</sub> =500mA, V <sub>GS</sub> =10V, R <sub>G</sub> =6Ω (Note 1,2)	-	2.2	5	ns
Turn-On Rise Time	t <sub>r</sub>		-	19.2	38	
Turn-Off Delay Time	t <sub>d(off)</sub>		-	6.2	12	
Turn-Off Fall Time	t <sub>f</sub>		-	23	50	
<b>Drain-Source Diode</b>						
Maximum Continuous Drain-Source Diode Forward Current	I <sub>S</sub>	---	-	-	500	mA
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =500mA, V <sub>GS</sub> =0V	-	0.86	1.5	V

NOTES :

1. Pulse width ≤ 300us, Duty cycle ≤ 2%.
2. Essentially independent of operating temperature typical characteristics.
3. R<sub>θJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. mounted on a 1 inch square pad of copper.

# PJT138K

## TYPICAL CHARACTERISTIC CURVES

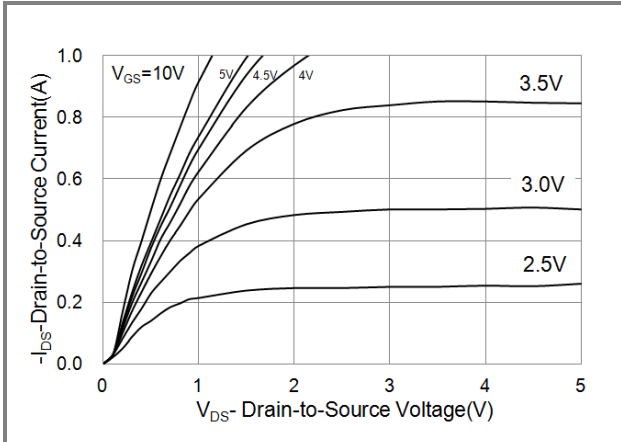


Fig.1 On-Region Characteristics

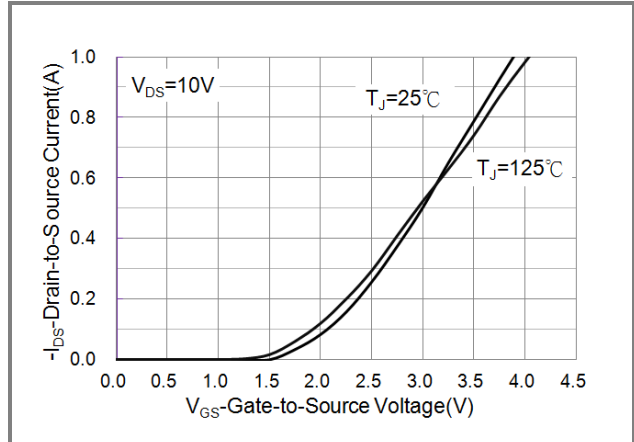


Fig.2 Transfer Characteristics

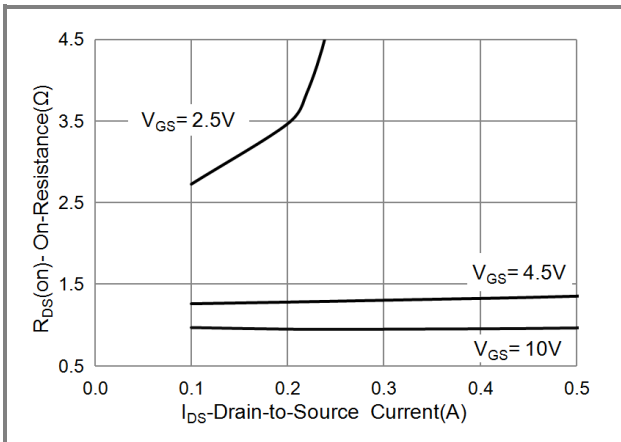


Fig.3 On-Resistance vs. Drain Current

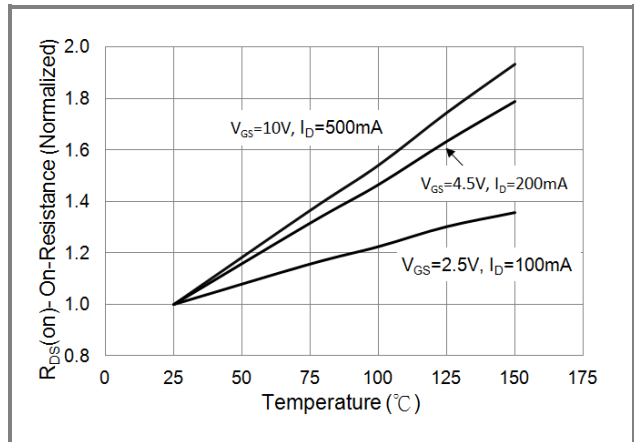


Fig.4 On-Resistance vs. Junction temperature

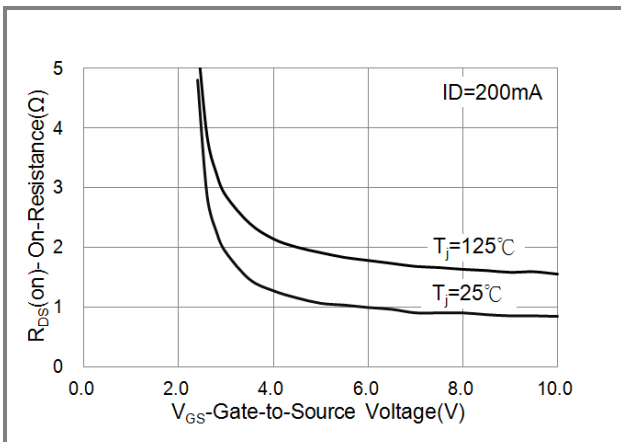


Fig.5 On-Resistance Variation with VGS.

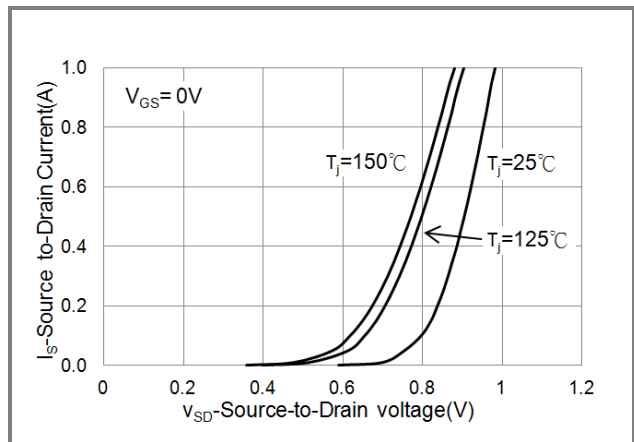
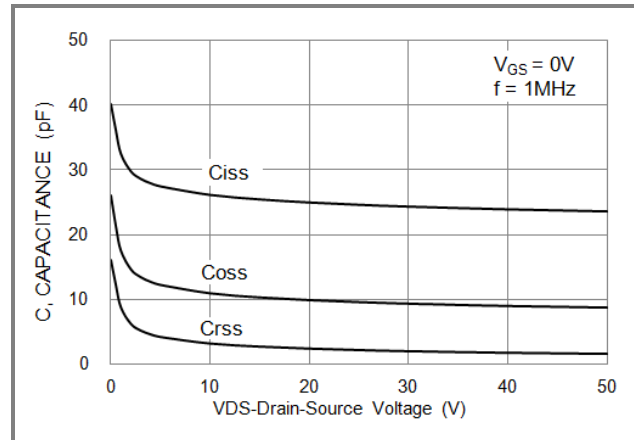
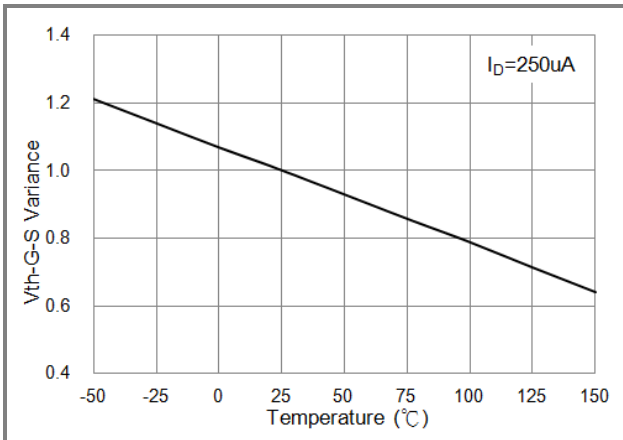
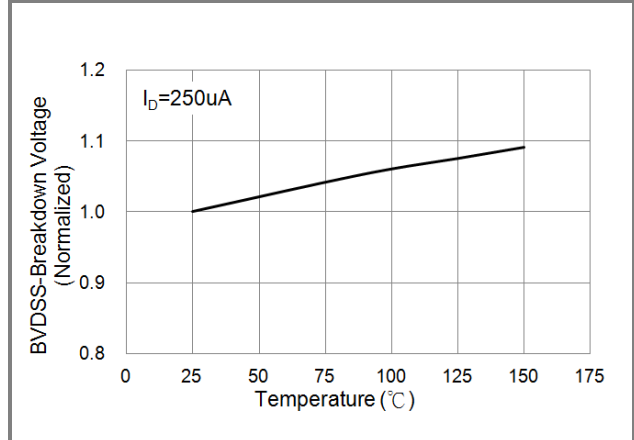
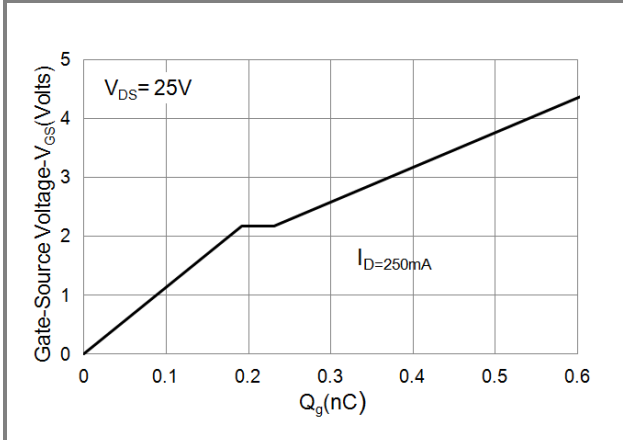


Fig.6 Body Diode Characteristics

# PJT138K

## TYPICAL CHARACTERISTIC CURVES

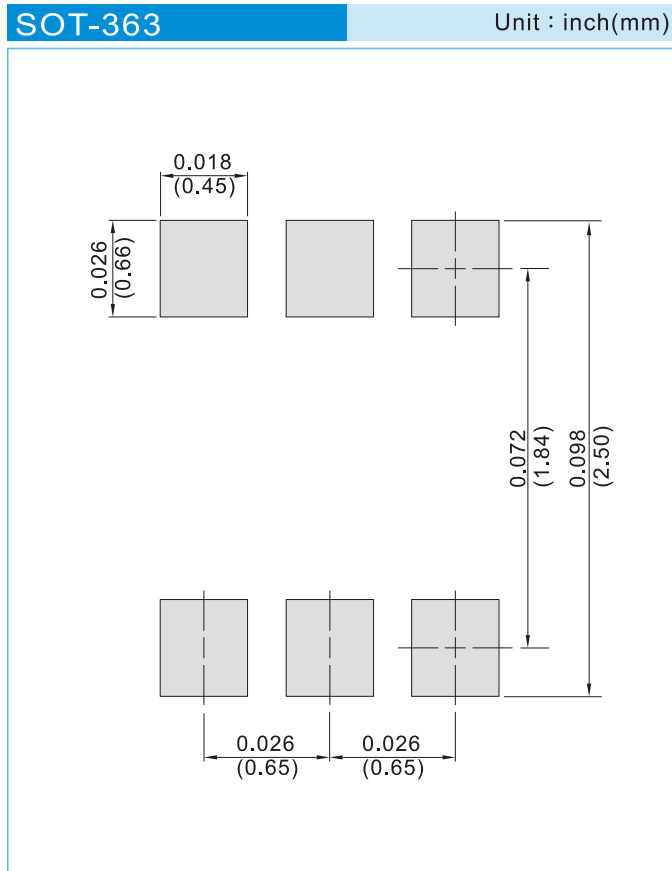


# PJT138K

## Product and Packing Information

Part No.	Package Type	Packing Type	Marking
PJT138K	SOT-363	3K pcs / 7" reel	8KD
PJT138K	SOT-363	10K pcs / 13" reel	8KD

## MOUNTING PAD LAYOUT



## PJT138K

### Disclaimer

- Reproducing and modifying information of the document is prohibited without permission from Panjit International Inc..
- Panjit International Inc. reserves the rights to make changes of the content herein the document anytime without notification. Please refer to our website for the latest document.
- Panjit International Inc. disclaims any and all liability arising out of the application or use of any product including damages incidentally and consequentially occurred.
- Panjit International Inc. does not assume any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.
- Applications shown on the herein document are examples of standard use and operation. Customers are responsible in comprehending the suitable use in particular applications. Panjit International Inc. makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.
- The products shown herein are not designed and authorized for equipments requiring high level of reliability or relating to human life and for any applications concerning life-saving or life-sustaining, such as medical instruments, transportation equipment, aerospace machinery et cetera. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Panjit International Inc. for any damages resulting from such improper use or sale.
- Since Panjit uses lot number as the tracking base, please provide the lot number for tracking when complaining.